

Fig. 2A

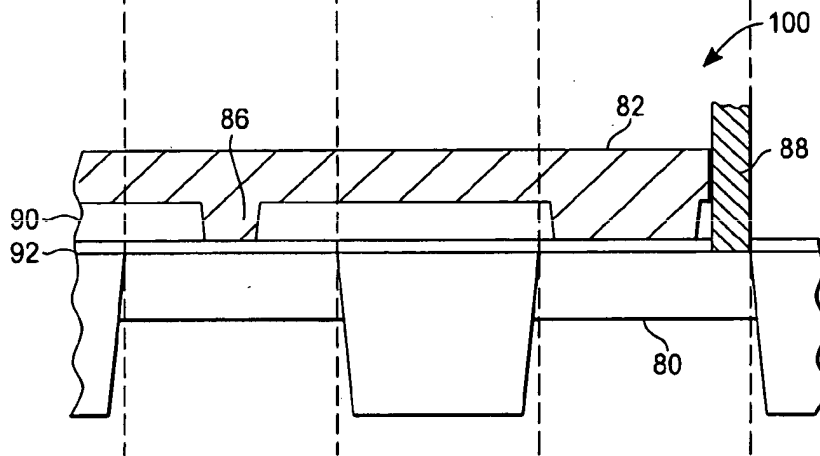


Fig. 2B

EEPROM CELL (A-A)

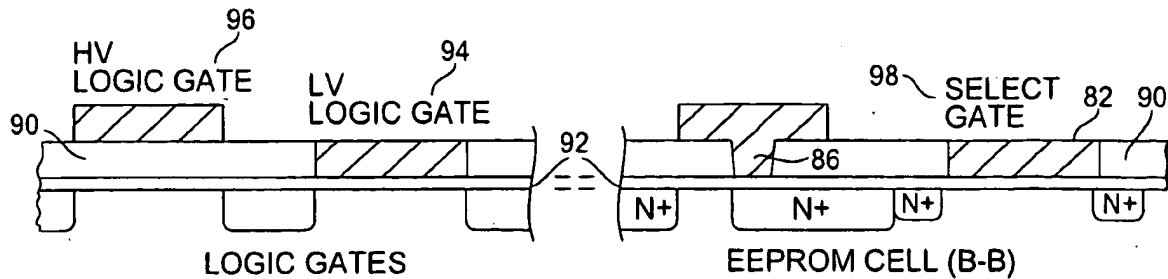


Fig. 2C

+

Second Area
ATM-262 Device

REPLACEMENT SHEET
Third Area Device

First Area Device

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HIGH VOLTAGE MOS

LOW VOLTAGE MOS

EEPROM CELL ALONG WORDLINE

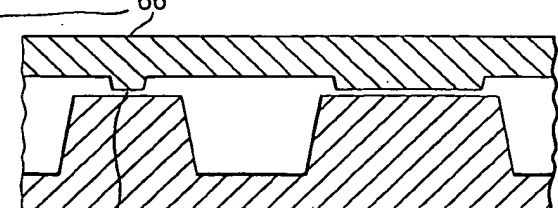
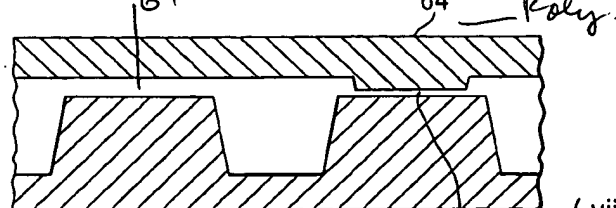
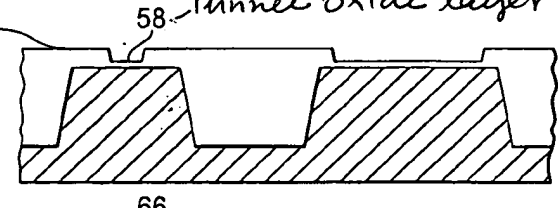
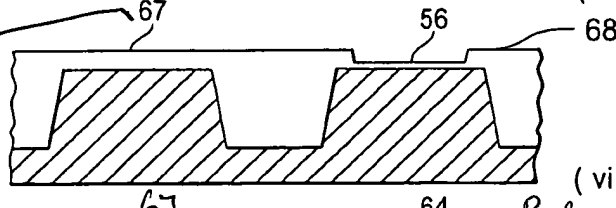
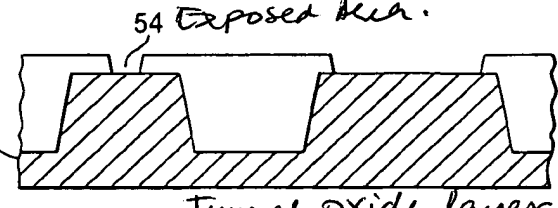
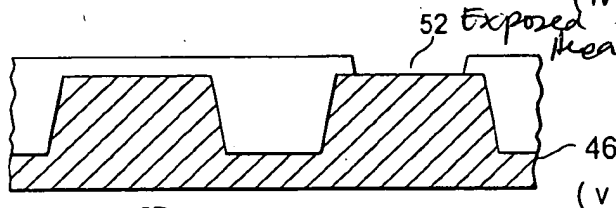
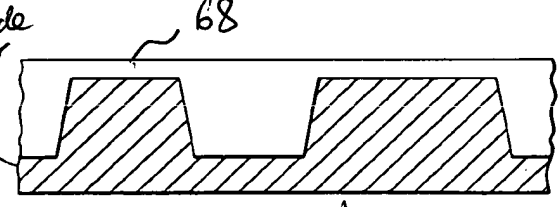
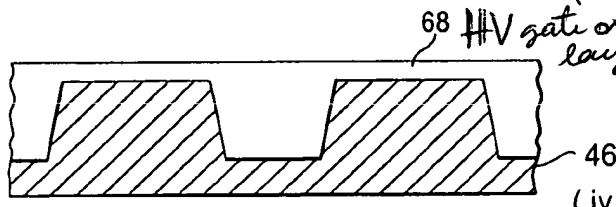
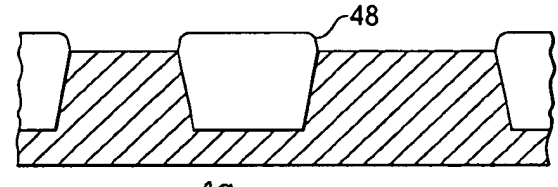
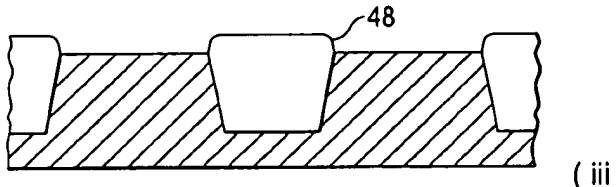
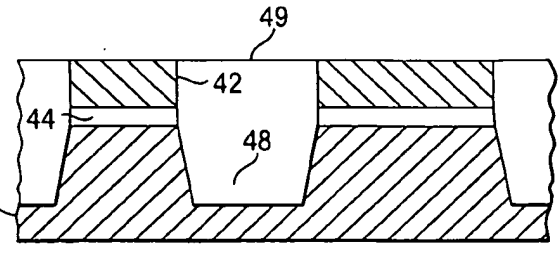
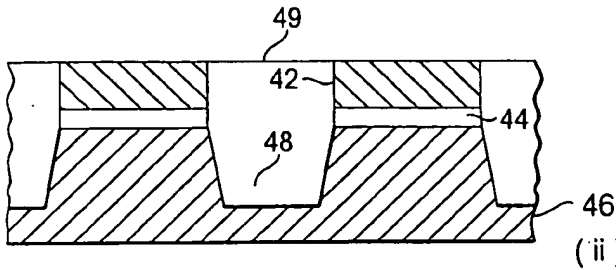
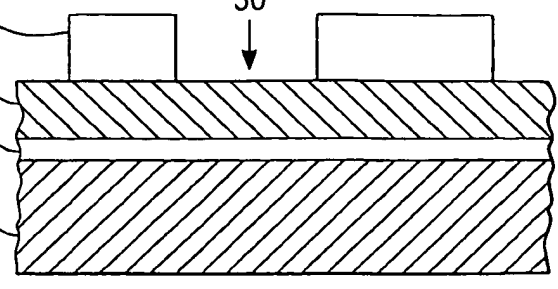
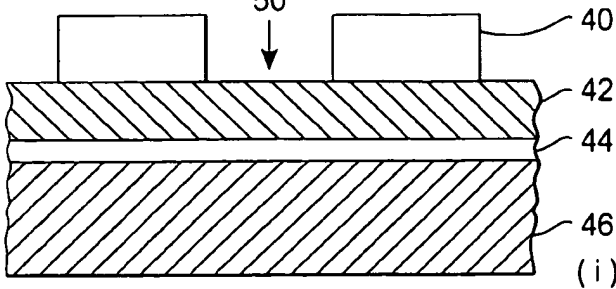


Fig. 3A

Fig. 3B

LV gate oxide layer

56

58

+

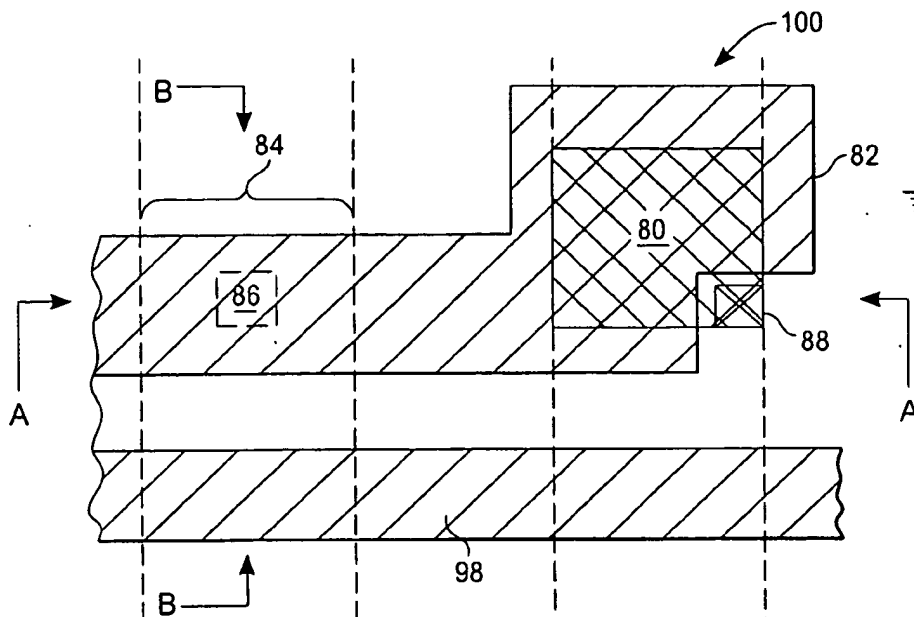


Fig. 2A

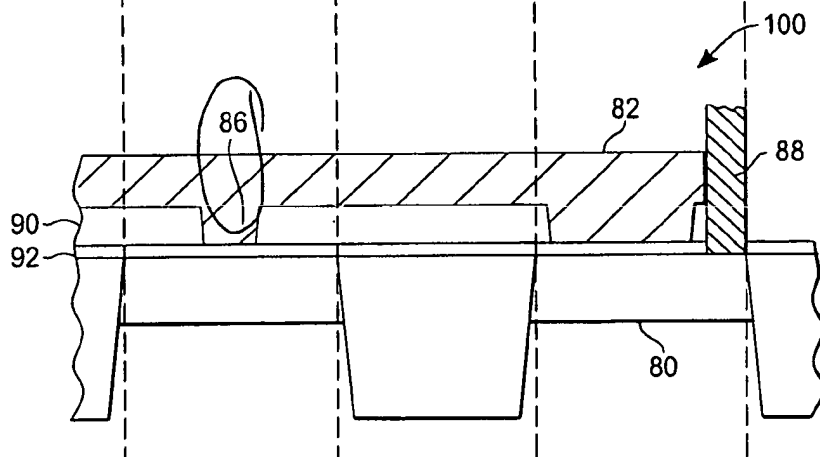


Fig. 2B

EEPROM CELL (A-A)

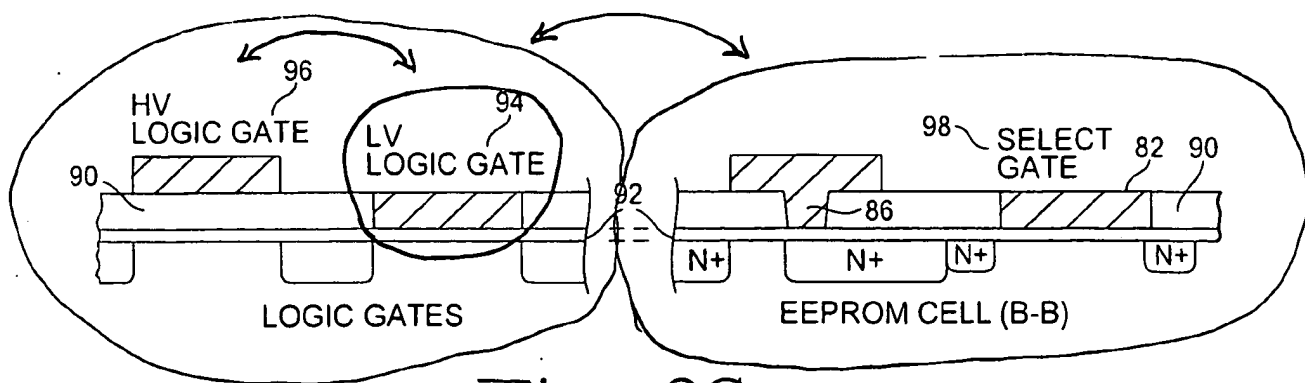


Fig. 2C

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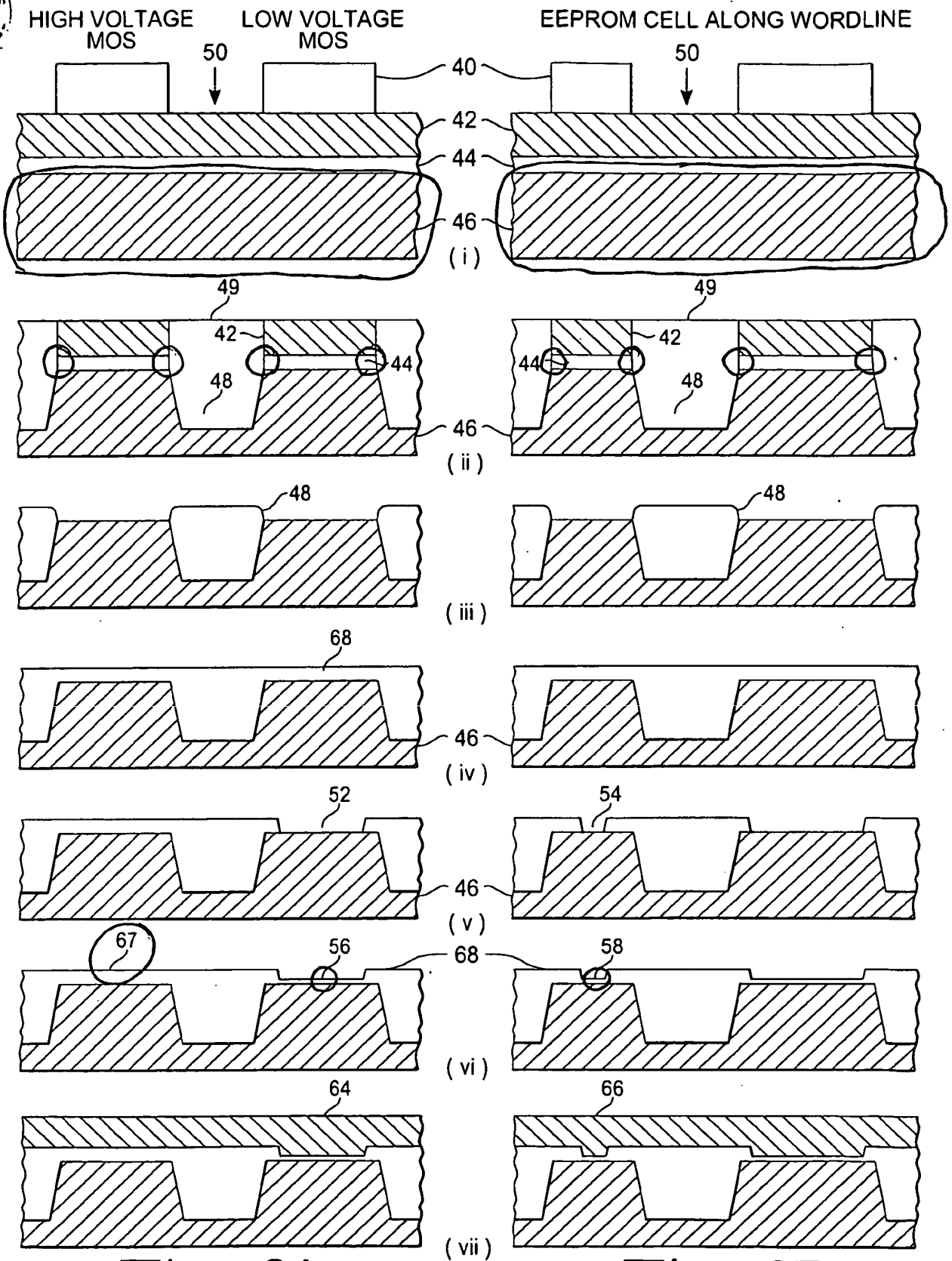


Fig. 3A

Fig. 3B